2 A, 40 V Schottky Barrier **Diode**

These Schottky barrier diodes are optimized for low forward voltage drop and low leakage current and are offered in a Chip Scale Package (CSP) to reduce board space. The low thermal resistance enables designers to meet the challenging task of achieving higher efficiency and meeting reduced space requirements.

Features

- Low Forward Voltage Drop 520 mV (Typ.) @ $I_F = 2 A$
- Low Reverse Current 35 μ A (Typ.) @ $V_R = 40 \text{ V}$
- 2 A of Continuous Forward Current
- ESD Rating Human Body Model: Class 3B
 - Machine Model: Class C
- High Switching Speed
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- LCD and Keypad Backlighting
- Camera Photo Flash
- Buck and Boost dc-dc Converters
- Reverse Voltage and Current Protection
- Clamping & Protection

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	VR	40	V
Forward Current (DC)	ÎF	2	Α
Forward Surge Current (60 Hz @ 1 cycle)	IFSM	19	Α
Repetitive Peak Forward Current (Pulse Wave = 1 sec, Duty Cycle = 66%)	I _{FRM}	3.4	Α
ESD Rating: Human Body Model Machine Model	ESD	> 8 > 400	kV V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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MARKING DIAGRAM

PIN 1

DSN₂ (0603)CASE 152AT 6TM

= Specific Device Code Date Code

ORDERING INFORMATION

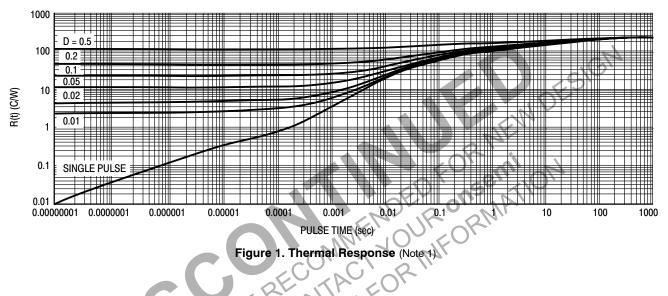
Device	Package	Shipping [†]
NSR20406NXT5G	DSN2 (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Max	Unit
Thermal Resistance Junction-to-Ambient (Note 1) Total Power Dissipation @ T _A = 25°C	R _{θJA} P _D			245 510	°C/W mW
Thermal Resistance Junction-to-Ambient (Note 2) Total Power Dissipation @ T _A = 25°C	R _{θJA} P _D			90 1.4	°C/W W
Storage Temperature Range	T _{stg}			-40 to +125	°C
Junction Temperature	TJ			+150	°C

- 1. Mounted onto a 4 in square FR-4 board 50 mm sq. 1 oz. Cu 0.06" thick single sided. Operating to steady state.
- 2. Mounted onto a 4 in square FR-4 board 650 mm sq. 1 oz. Cu 0.06" thick single sided. Operating to steady state.



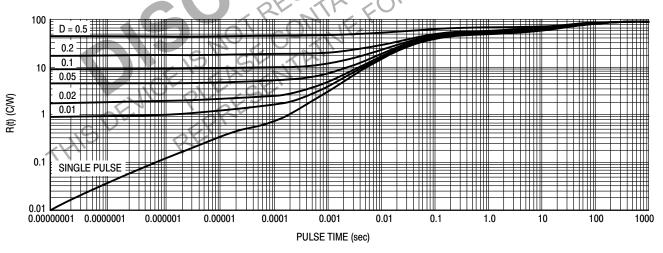
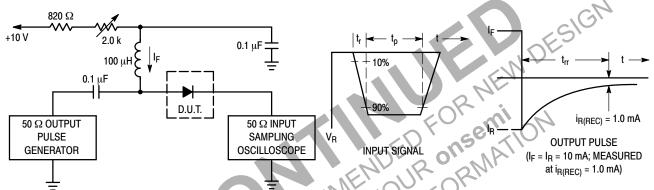


Figure 2. Thermal Response (Note 2)

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Leakage (V _R = 10 V) (V _R = 40 V)	I _R	- -	3 35	15 150	μА
Forward Voltage $(I_F = 10 \text{ mA})$ $(I_F = 100 \text{ mA})$ $(I_F = 500 \text{ mA})$ $(I_F = 500 \text{ mA})$ $(I_F = 1 \text{ A})$ $(I_F = 2 \text{ A})$	V _F	- - - -	240 310 380 430 520	280 350 420 470 550	mV
Total Capacitance (V _R = 2.0 V, f = 1.0 MHz)	C _T	-	140	-	pF
Reverse Recovery Time (I _F = I _R = 10 mA, I _{R(REC)} = 1.0 mA, Figure 3)	t _{rr}	_	53	-	ns
Peak Forward Recovery Voltage (I _F = 100 mA, t _r = 20 ns, Figure 4)	V_{FRM}	_	440	-	mV

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



Notes: 1. A 2.0 k Ω variable resistor adjusted for a Forward Current (I_F) of 10 mA. 2. Input pulse is adjusted so I_{R(peak)} is equal to 10 mA.

Figure 3. Recovery Time Equivalent Test Circuit

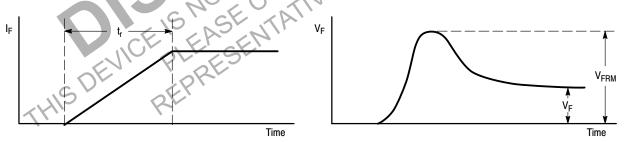


Figure 4. Peak Forward Recover Voltage Definition

TYPICAL CHARACTERISTICS

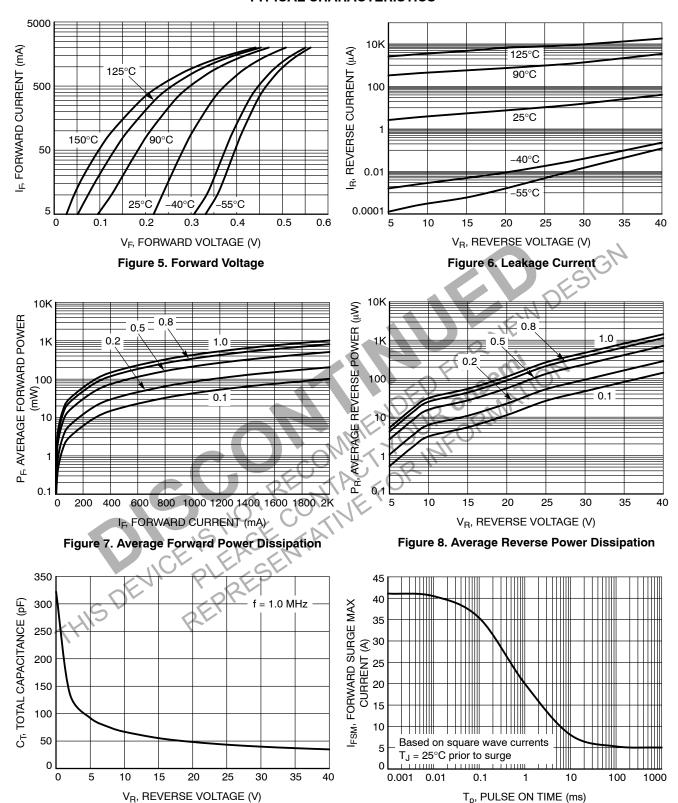


Figure 10. Forward Surge Maximum

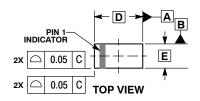
Figure 9. Total Capacitance

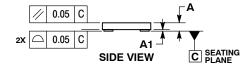


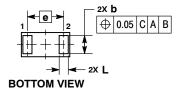


DSN2, 1.6x0.8, 1.2P, (0603) CASE 152AT ISSUE A

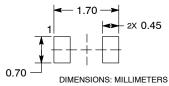
DATE 03 JUN 2016







RECOMMENDED MOUNTING FOOTPRINT*



See Application Note AND8464/D for more mounting details

NOTES:

- DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.25	0.31	
A1	0.00	0.05	
b	0.55	0.65	
D	1.60 BSC		
Е	0.80 BSC		
е	1.20 BSC		
L	0.25 0.35		

GENERIC MARKING DIAGRAM1*



XXXX = Specific Device Code YYY = Year Code

GENERIC MARKING DIAGRAM2*

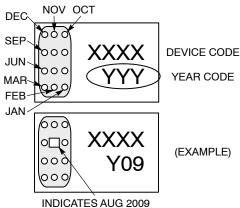


XX = Specific Device Code

M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

CATHODE BAND MONTH CODING



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^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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